

CLAIM AMENDMENTS

Please amend the claims by canceling claims 1-9 and 13, amending claims 10-12, and adding new claims 14 and 15, all without prejudice, as indicated on the following listing of all the claims in the present application after this Amendment:

1 – 9. (Cancelled)

10. (Currently Amended) In a flash memory system having an array of non-volatile memory cells arranged in blocks as a unit of erase, pages therein as a unit of data programming and reading, and planes of a plurality of blocks that are independently accessible, a method of operation, comprising:

logically forming metablocks that individually include a block from a plurality of the planes,

sequentially receiving write commands with varying amounts of data, and variously writing the received data in parallel either sequentially into pages within individual blocks of only one of the planes or in parallel into pages within two or more blocks of one of the metablocks in two or more planes in response to varying characteristics of the host write commands.

11. (Currently Amended) The method of claim 10, additionally comprising writing an indication into non-volatile memory cells at the same time as the received data that identifies the blocks into which the data are being written in parallel.

12. (Currently Amended) In a non-volatile memory system having an array of memory cells organized into blocks of cells that are erasable together and which individually store a plurality of units of data, a method of responding to a series of write commands that individually designate a logical address of one or more units of data to be written and which are accompanied by the designated one or more units of data being received sequentially, comprising:

converting the logical address of an individual write command into a physical address within one or more of the blocks of memory cells that allow writing the accompanying one or more units of data in parallel, wherein a number of said one or more blocks are selected for receiving said one or more units of data as a function of the number of units of data specified by at least one of the received series of write commands, the number of units of data specified by individual ones of the received series of write commands varying, and

writing the selected one or more units of data into said one or more blocks in parallel.

13. (Cancelled)

14. (New) In a flash memory system having an array of non-volatile memory cells arranged in a plurality of blocks of memory cells as a unit of erase that are provided in a plurality of sub-arrays and multiple pages within individual blocks as units of data programming and reading, a method of operation, comprising:

logically forming metablocks that individually include blocks from a plurality of the sub-arrays,

sequentially receiving individual write commands with a number of sectors of data to be written into either a single page or into a plurality of pages,

in response to receiving the write commands with a number of sectors of data for a plurality of pages, writing the received data in parallel into pages within a plurality of blocks of at least one of the metablocks in a plurality of the sub-arrays,

in response to receiving the write commands with a number of sectors of data for a single page of data, writing the received data in parallel into individual pages of individual blocks of the metablocks in only one of the sub-arrays, and

maintaining indications in the non-volatile memory cells that are associated with the written sectors of data as to whether the individual sectors have been written in logical sequence with other sectors in either (1) a single block or (2) a plurality of blocks of a metablock.

15. (New) The method of claim 14, wherein a FAT table is stored within the non-volatile memory cells and the sectors of data for a single page of data include data of the FAT table.